Advance Information

MC54/74HCT541A

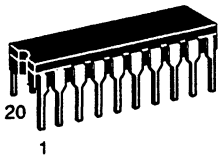
Octal 3-State Non-Inverting Buffer/Line Driver/Line Receiver With LSTTL-Compatible Inputs

High-Performance Silicon-Gate CMOS

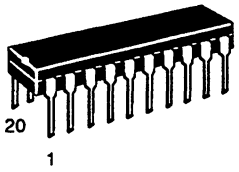
The MC54/74HCT541A is identical in pinout to the LS541. This device may be used as a level converter for interfacing TTL or NMOS outputs to high speed CMOS inputs.

The HCT541A is an octal non-inverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active-low output enables.

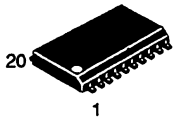
- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5V
- Low Input Current: 1μA
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 134 FETs or 33.5 Equivalent Gates



J SUFFIX
CERAMIC
CASE 732-03



N SUFFIX
PLASTIC
CASE 738-03



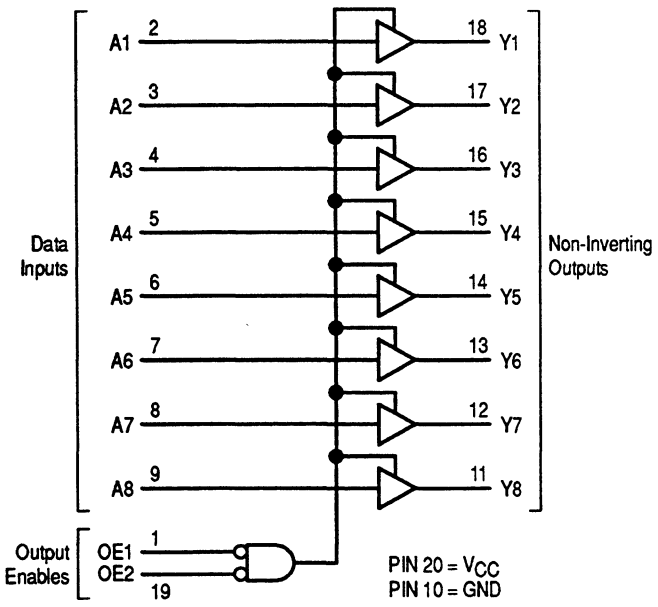
DW SUFFIX
SOIC
CASE 751D-04

ORDERING INFORMATION

MC74HCTXXXAN	Plastic
MC54HCTXXXAJ	Ceramic
MC74HCTXXXADW	SOIC Wide

T_A = –55° to 125°C for all packages.

LOGIC DIAGRAM



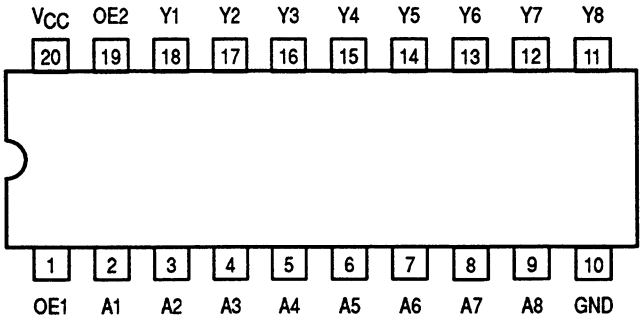
FUNCTION TABLE

Inputs			Output Y
OE1	OE2	A	
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

Z = High Impedance
X = Don't Care

This document contains information on a new product. Specifications and information herein are subject to change without notice.

Pinout: 20-Lead Packages (Top View)



MAXIMUM RATINGS*

Symbol	Characteristic		Range	Unit
V_{CC}	DC Supply Voltage	Referenced to GND	–0.5 to +7.0	V
V_{in}	DC Input Voltage	Referenced to GND	–0.5 to V_{CC} + 0.5	V
V_{out}	DC Output Voltage	Referenced to GND	–0.5 to V_{CC} + 0.5	V
I_{in}	DC Input Current, per Pin		±20	mA
I_{out}	DC Output Current, per Pin		±35	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins		±75	mA
P_D	Power Dissipation in Still Air	Plastic or Ceramic DIP† SOIC Package†	750 500	mW
T_{stg}	Storage Temperature Range		–65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds	Plastic DIP or SOIC Package Ceramic DIP	260 300	°C

* Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

† Derating — Plastic DIP: –10mW/°C from 65° to 125°C
Ceramic DIP: –10mW/°C from 100° to 125°C
SOIC Package: –7mW/°C from 65° to 125°C

For high frequency or heavy load considerations, refer to Chapter 4 in the High-Speed CMOS Data Book (DL129/D).

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must be tied to and appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage	Referenced to GND	4.5	5.5	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage	Referenced to GND	0	V_{CC}	V
T_A	Operating Temperature Range, All Package Types		–55	+125	°C
t_r, t_f	Input Rise/Fall Time	(Figure 1)	0	500	ns

DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V_{CC} V	Guaranteed Limit			Unit
				–55 to 25°C	≤85°C	≤125°C	
V_{IH}	Minimum High-Level Input Voltage	V_{out} = 0.1V or V_{CC} – 0.1V $\|I_{out}\| \le 20\mu A$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V_{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1V or V_{CC} – 0.1V $\|I_{out}\| \le 20\mu A$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V_{OH}	Minimum High-Level Output Voltage	V_{in} = V_{IH} or V_{IL} $\|I_{out}\| \le 20\mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		V_{in} = V_{IH} or V_{IL} $\|I_{out}\| \le 6.0mA$	4.5	3.98	3.84	3.70	
V_{OL}	Maximum Low-Level Output Voltage	V_{in} = V_{IH} or V_{IL} $\|I_{out}\| \le 20\mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		V_{in} = V_{IH} or V_{IL} $\|I_{out}\| \le 6.0mA$	4.5	0.26	0.33	0.40	
I_{in}	Maximum Input Leakage Current	V_{in} = V_{CC} or GND	5.5	±0.1	±1.0	±1.0	μA
I_{OZ}	Maximum Three-State Leakage Current	Output in High Impedance State V_{in} = V_{IL} or V_{IH} V_{out} = V_{CC} or GND	5.5	±0.5	±5.0	±10.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{in} = V_{CC} or GND I_{out} = 0μA	5.5	4	40	160	μA

ΔI_{CC}	Additional Quiescent Supply Current	V_{in} = 2.4V, Any One Input V_{in} = V_{CC} or GND, Other Inputs I_{out} = 0μA		≥ –55°C	25 to 125°C	
			5.5	2.9	2.4	mA

1. Information on typical parametric values can be found in Chapter 4 of the High-Speed CMOS Data Book (DL129/D).
2. Total Supply Current = $I_{CC} + \Sigma\Delta I_{CC}$.

AC CHARACTERISTICS (V_{CC} = 5.0V, C_L = 50pF, Input $t_r = t_f$ = 6ns)

Symbol	Parameter	Guaranteed Limit			Unit
		–55 to 25°C	≤85°C	≤125°C	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	23	28	32	ns
t_{PLZ}, t_{PHZ}	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	30	34	38	ns
t_{PZL}, t_{PZH}	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	30	34	38	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	12	15	18	ns
C_{in}	Maximum Input Capacitance	10	10	10	pF
C_{out}	Maximum Three-State Output Capacitance (Output in High Impedance State)	15	15	15	pF

NOTE: For propagation delays with loads other than 50pF, and information on typical parametric values, see Chapter 4 of the High-Speed CMOS Data Book (DL129/D).

AC CHARACTERISTICS (C_L = 50pF, Input $t_r = t_f$ = 6ns)

Symbol	Parameter	Typical at 25°C, V_{CC} = 5.0V	Unit
C_{PD}	Power Dissipation Capacitance (Per Buffer)*	55	pF

* Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 4 of the High-Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS

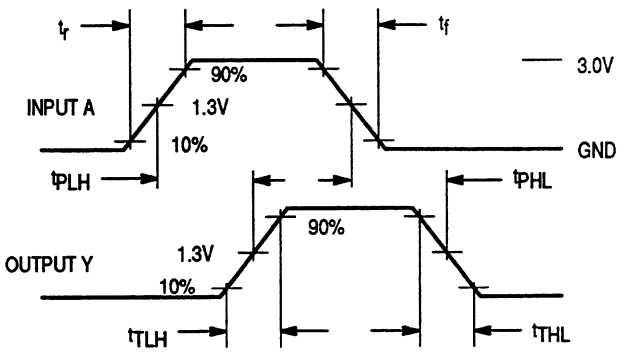


Figure 1.

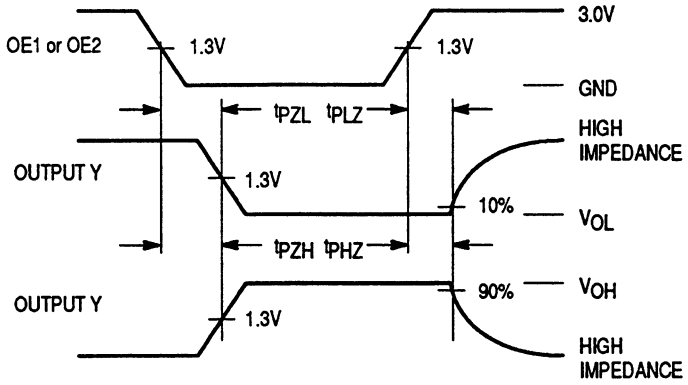
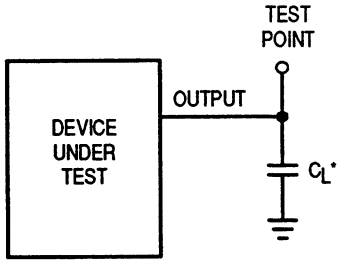


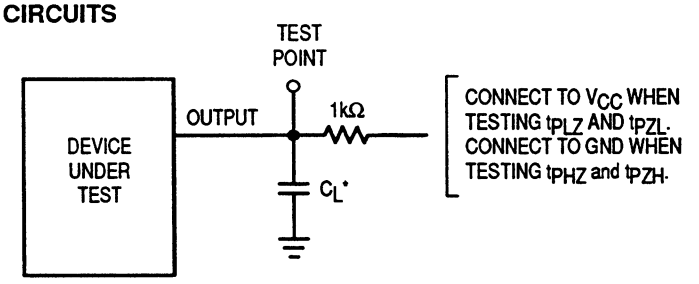
Figure 2.

TEST CIRCUITS



*Includes all probe and jig capacitance

Figure 3.



*Includes all probe and jig capacitance

Figure 4.

PIN DESCRIPTIONS

INPUTS

A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9) — Data input pins. Data on these pins appear in non-inverted form on the corresponding Y outputs, when the outputs are enabled.

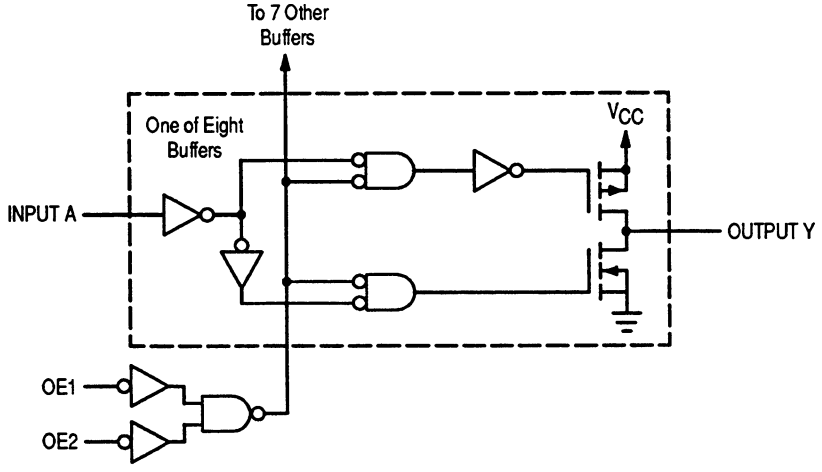
CONTROLS

OE1, OE2 (PINS 1, 19) — Output enables (active-low). When a low voltage is applied to both of these pins, the outputs are enabled and the device functions as a non-inverting buffer. When a high voltage is applied to either input, the outputs assume the high impedance state.

OUTPUTS

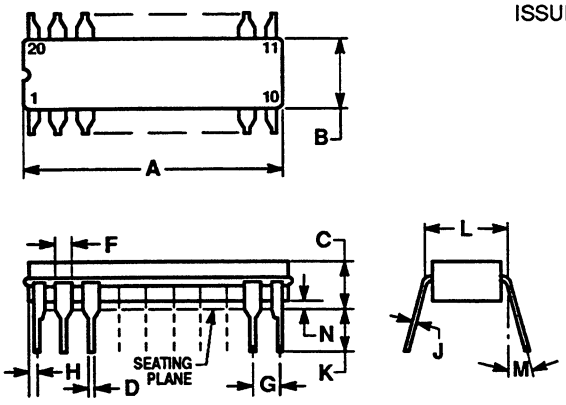
Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11) — Device outputs. Depending upon the state of the output enable pins, these outputs are either non-inverting outputs or high-impedance outputs.

LOGIC DETAIL



OUTLINE DIMENSIONS

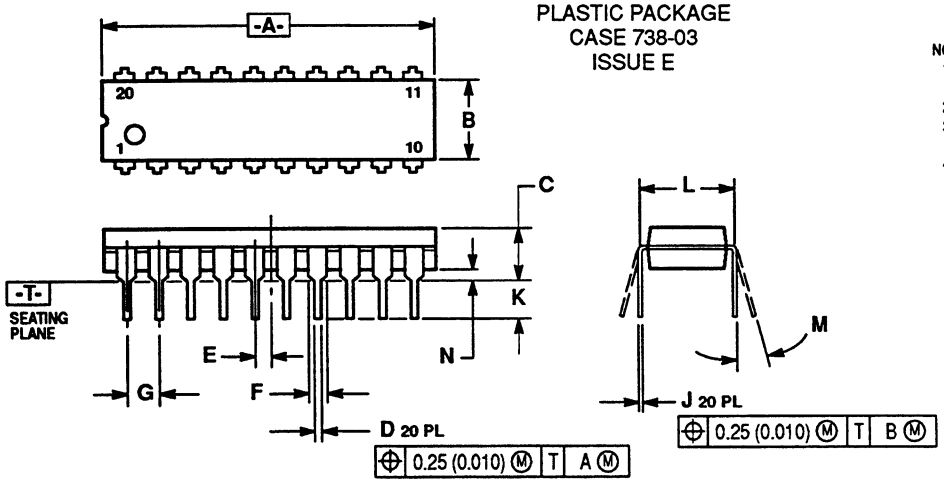
J SUFFIX
CERAMIC PACKAGE
CASE 732-03
ISSUE E



NOTES:
1. LEADS WITHIN 0.25 (0.010) DIAMETER, TRUE POSITION AT SEATING PLANE, AT MAXIMUM MATERIAL CONDITION.
2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
3. DIMENSIONS A AND B INCLUDE MENISCUS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	23.88	25.15	0.940	0.990
B	6.60	7.49	0.260	0.295
C	3.81	5.08	0.150	0.200
D	0.38	0.56	0.015	0.022
F	1.40	1.65	0.055	0.065
G	2.54 BSC		0.100 BSC	
H	0.51	1.27	0.020	0.050
J	0.20	0.30	0.008	0.012
K	3.18	4.06	0.125	0.160
L	7.62 BSC		0.300 BSC	
M	0°	15°	0°	15°
N	0.25	1.02	0.010	0.040

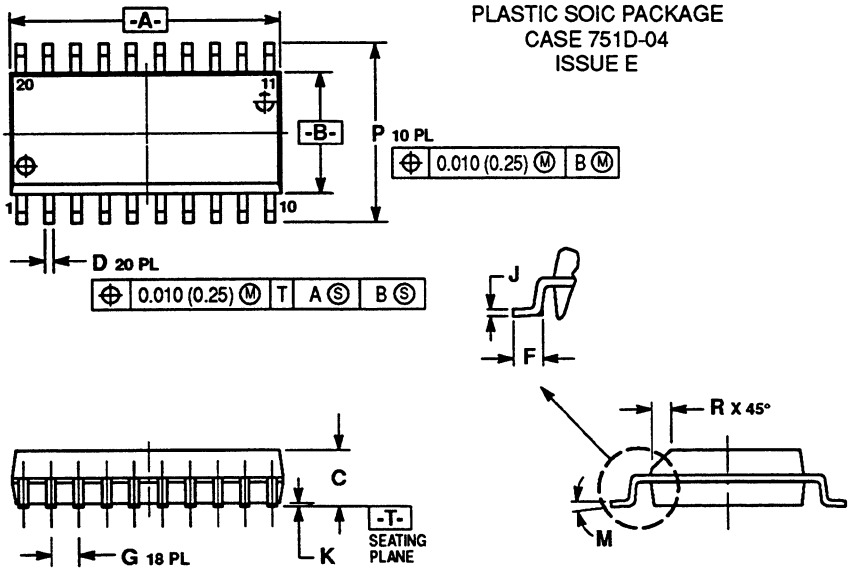
N SUFFIX
PLASTIC PACKAGE
CASE 738-03
ISSUE E



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.010	1.070	25.66	27.17
B	0.240	0.260	6.10	6.60
C	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050 BSC		1.27 BSC	
F	0.050	0.070	1.27	1.77
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

DW SUFFIX
PLASTIC SOIC PACKAGE
CASE 751D-04
ISSUE E



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.150 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	12.65	12.95	0.499	0.510
B	7.40	7.60	0.292	0.299
C	2.35	2.65	0.093	0.104
D	0.35	0.49	0.014	0.019
F	0.50	0.90	0.020	0.035
G	1.27 BSC		0.050 BSC	
J	0.25	0.32	0.010	0.012
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	10.05	10.55	0.395	0.415
R	0.25	0.75	0.010	0.029

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